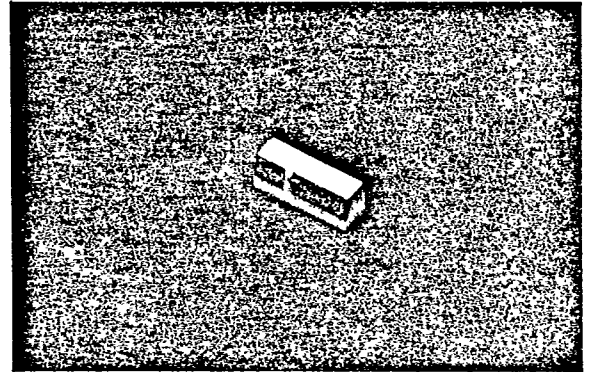


TOSHIBA PIN PHOTODIODE TOPD300

Features

- InGaAs PIN Structure
- Mesa Type
- Chip-carrier
- Wavelength 0.8~1.6 μ m
- High Speed 0.5ns Max
- Low Dark Current 10nA Max
- High Reliability



Package: F

Absolute Maximum Ratings (T_c = 25°C)

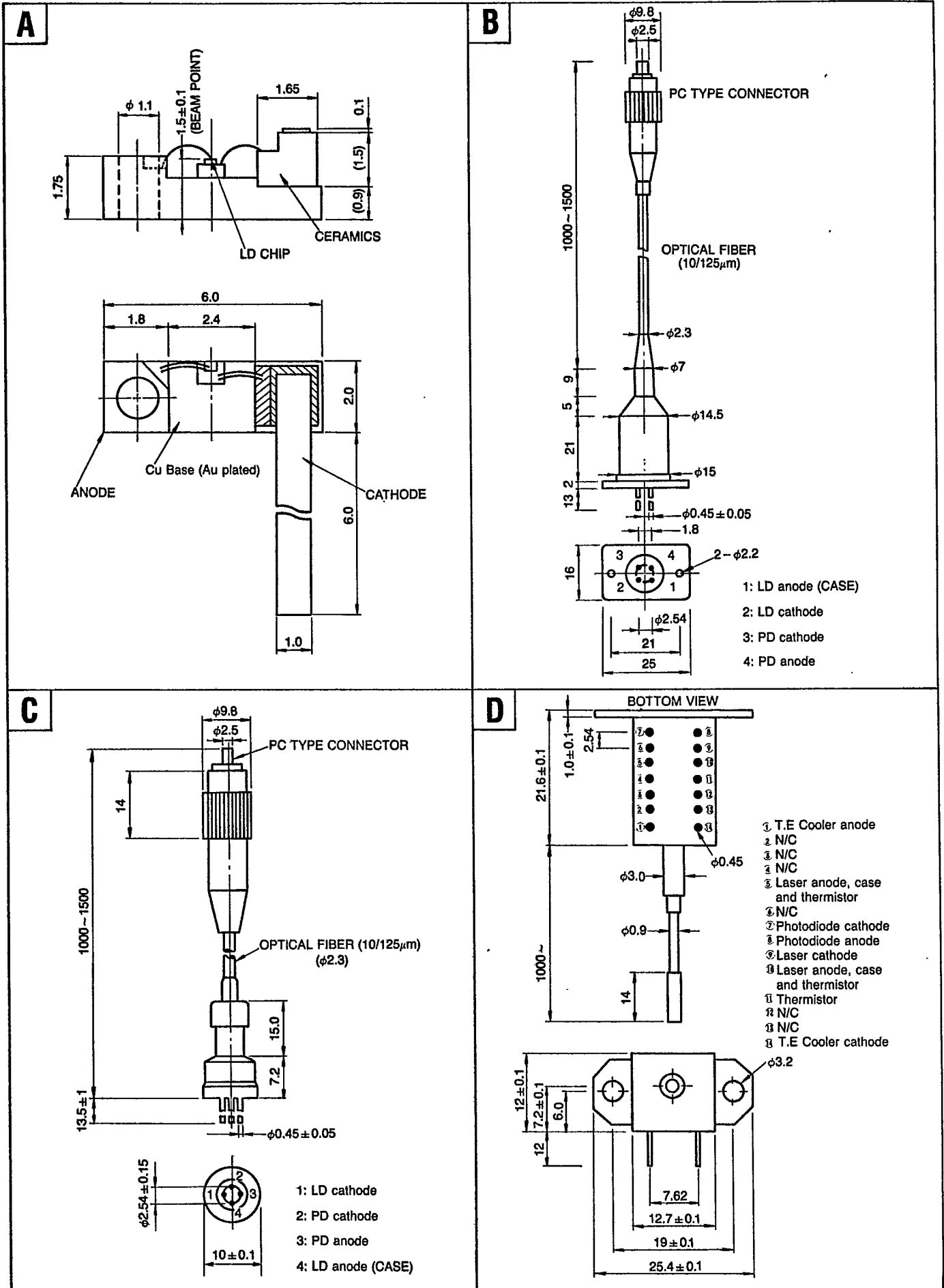
Item	Symbol	Ratings	Unit
Storage Temperature	T _{stg}	-40 ~ +100	°C
Operating Temperature	T _{opr}	-20 ~ +85	°C
Forward Current	I _{FL}	5	mA
Reverse Voltage	V _{RL}	30	V
Reverse Current	I _{RL}	50	μ A

Electrical and Optical Characteristics (T_c = 25°C)

Item	Symbol	Conditions	Min	Typ	Max	Unit
Responsivity	R	$\lambda = 13000\text{nm}$, V _R = 5V	0.5	0.7		A/W
		$\lambda = 1550\text{nm}$, V _R = 5V	0.55	0.77		A/W
Dark Current	I _d	V _R = 5V	—	5	10	nA
Rise Time	t _r	10-90%, V _R = 5V	—	0.3	0.5	ns
Fall Time	t _f	10-90%, V _R = 5V	—	0.3	0.5	ns
Capacitance	C _t	f = 1MHz, V _R = 5V	—	1	1.4	pF
Cutoff Frequency	f _c	V _R = 5V, -3dB	1	—	—	GHz

Outline Drawings

Unit mm



Unit mm

